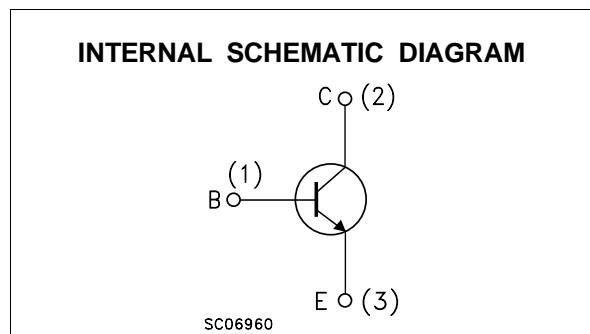
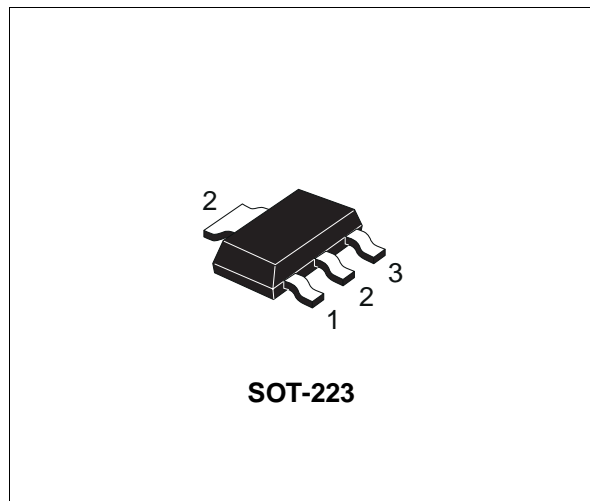


MEDIUM POWER AMPLIFIER

ADVANCE DATA

- SILICON EPITAXIAL PLANAR NPN TRANSISTORS
- MINIATURE PLASTIC PACKAGE FOR APPLICATION IN SURFACE MOUNTING CIRCUITS
- GENERAL PURPOSE MAINLY INTENDED FOR USE IN MEDIUM POWER INDUSTRIAL APPLICATION AND FOR AUDIO AMPLIFIER OUTPUT STAGE
- PNP COMPLEMENTS ARE STZT2907 AND STZT2907A RESPECTIVELY



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STZT2222	STZT2222A	
V _{CBO}	Collector-Base Voltage (I _E = 0)	60	75	V
V _{CEO}	Collector-Emitter Voltage (I _B = 0)	30	40	V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	5	6	V
I _C	Collector Current	0.8		A
P _{tot}	Total Dissipation at T _c = 25 °C	1.5		W
T _{stg}	Storage Temperature	-65 to 150		°C
T _j	Max. Operating Junction Temperature	150		°C

STZT2222/STZT2222A

THERMAL DATA

$R_{thj-amb}$	Thermal Resistance Junction-Ambient	Max	83.3	$^{\circ}\text{C}/\text{W}$
$R_{thj-tab}$	Thermal Resistance Junction-Collector Tab	Max	10	$^{\circ}\text{C}/\text{W}$

• Mounted on a ceramic substrate area = 30 x 35 x 0.7 mm

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-off Current ($I_E = 0$)	$V_{CB} = \text{rated } V_{CBO}$ $V_{CB} = \text{rated } V_{CBO} \quad T_{amb} = 125^{\circ}\text{C}$			10 10	nA μA
I_{CEX}	Collector Cut-off Current ($V_{BE} = -3\text{V}$)	$V_{CE} = 60\text{ V}$ for STZT2222A			10	nA
I_{BEX}	Base Cut-off Current ($V_{BE} = -3\text{V}$)	$V_{CE} = 60\text{ V}$ for STZT2222A			20	nA
I_{EBO}	Emitter Cut-off Current ($I_E = 0$)	$V_{EB} = 3\text{ V}$ for STZT2222 for STZT2222A			30 15	nA nA
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ($I_E = 0$)	$I_C = 10\ \mu\text{A}$ for STZT2222 for STZT2222A	60 75			V V
$V_{(BR)CEO}^*$	Collector-Emitter Breakdown Voltage ($I_B = 0$)	$I_C = 10\text{ mA}$ for STZT2222 for STZT2222A	30 40			V V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_C = 0$)	$I_E = 10\ \mu\text{A}$ for STZT2222 for STZT2222	5 6			V V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = 150\text{ mA} \quad I_B = 15\text{ mA}$ for STZT2222 for STZT2222A $I_C = 500\text{ mA} \quad I_B = 50\text{ mA}$ for STZT2222 for STZT2222A			0.4 0.3 1.6 1	V V V V
$V_{BE(sat)}^*$	Base-Emitter Saturation Voltage	$I_C = 150\text{ mA} \quad I_B = 15\text{ mA}$ for STZT2222 for STZT2222A $I_C = 500\text{ mA} \quad I_B = 50\text{ mA}$ for STZT2222 for STZT2222A		0.6	1.3 1.2 2.6 2	V V V V
h_{FE}^*	DC Current Gain	$I_C = 0.1\text{ mA} \quad V_{CE} = 10\text{ V}$ $I_C = 1\text{ mA} \quad V_{CE} = 10\text{ V}$ $I_C = 10\text{ mA} \quad V_{CE} = 10\text{ V}$ $I_C = 150\text{ mA} \quad V_{CE} = 10\text{ V}$ $I_C = 150\text{ mA} \quad V_{CE} = 1\text{ V}$ $I_C = 500\text{ mA} \quad V_{CE} = 10\text{ V}$ for STZT2222 for STZT2222A $I_C = 10\text{ mA} \quad V_{CE} = 10\text{ V} \quad T_c = -55^{\circ}\text{C}$ for STZT2222	35 50 75 100 50 30 40 35		300	

ELECTRICAL CHARACTERISTICS ($T_{\text{case}} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

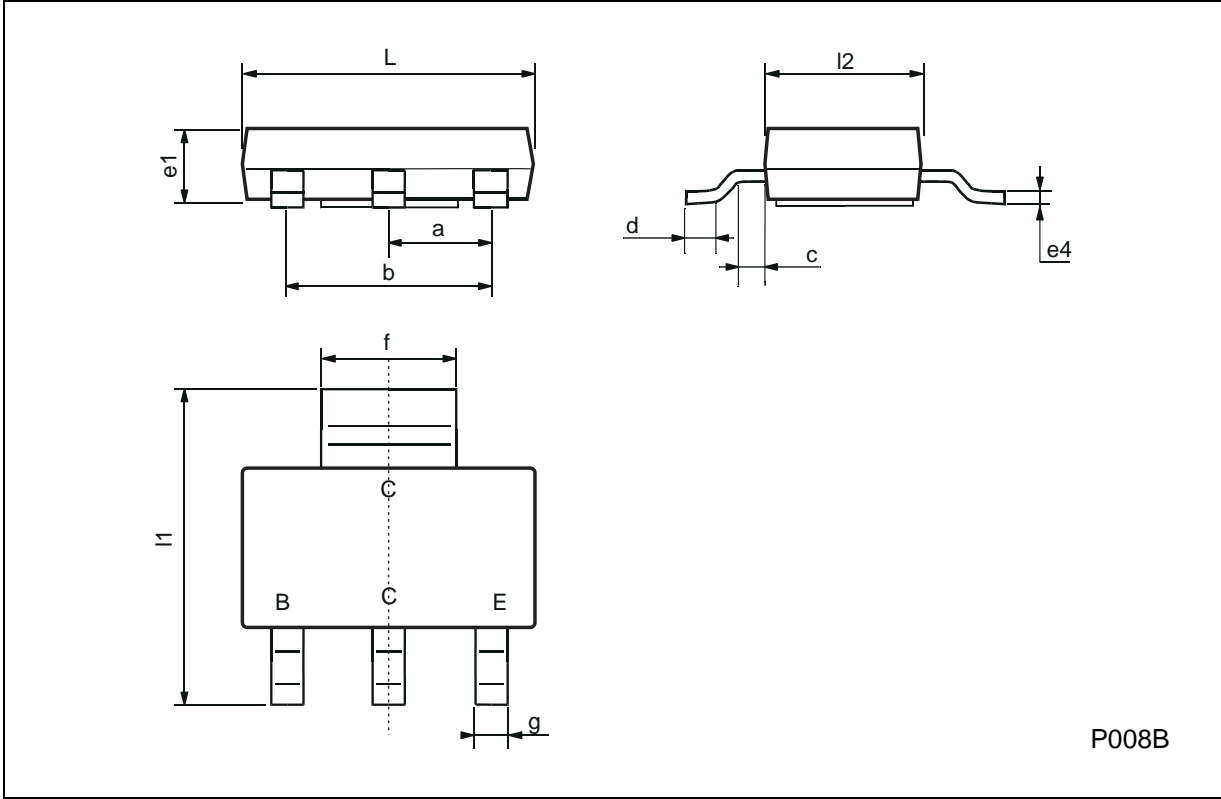
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
h_{fe} **	Small Signal Current Gain	$I_C = 1\text{ mA}$ $V_{CE} = 10\text{ V}$ $f = 1\text{ KHz}$ $I_C = 10\text{ mA}$ $V_{CE} = 10\text{ V}$ $f = 1\text{ KHz}$	50 75		300 375	$K\Omega$
h_{ie} **	Input Impedance	$I_C = 1\text{ mA}$ $V_{CE} = 10\text{ V}$ $f = 1\text{ KHz}$ $I_C = 10\text{ mA}$ $V_{CE} = 10\text{ V}$ $f = 1\text{ KHz}$	2 0.25		8 1.25	
h_{re} **	Reverse Voltage Ratio	$I_C = 1\text{ mA}$ $V_{CE} = 10\text{ V}$ $f = 1\text{ KHz}$ $I_C = 10\text{ mA}$ $V_{CE} = 10\text{ V}$ $f = 1\text{ KHz}$			8 4	10^{-4}
h_{oe} **	Output Impedance	$I_C = 1\text{ mA}$ $V_{CE} = 10\text{ V}$ $f = 1\text{ KHz}$ $I_C = 10\text{ mA}$ $V_{CE} = 10\text{ V}$ $f = 1\text{ KHz}$	5 25		35 375	S
f_T	Transition Frequency	$I_C = 10\text{ mA}$ $V_{CE} = 10\text{ V}$ $f = 100\text{ MHz}$ for STZT2222 for STZT2222A	250 300			MHz MHz
C_{CBO}	Collector-Base Capacitance	$I_E = 0$ $V_{CB} = 10\text{ V}$ $f = 1\text{ MHz}$			8	pF
C_{EBO}	Emitter-Base Capacitance	$I_C = 0$ $V_{EB} = 0.5\text{ V}$ $f = 1\text{ MHz}$ for STZT2222 for STZT2222A			30 25	pF pF
NF	Noise Figure	$f = 1\text{ KHz}$ $\Delta F = 200\text{ Hz}$ $R_G = 1K\Omega$ $I_C = 0.1\text{ mA}$ $V_{CE} = 10\text{ V}$			4	dB
t_d	Delay Time	$I_C = 150\text{ mA}$ $I_{C1} = 15\text{ mA}$			10	ns
t_r	Rise Time	$V_{BE} = -0.5\text{ V}$			25	ns
t_s	Storage Time	$I_C = 150\text{ mA}$ $I_{C1} = 15\text{ mA}$			225	ns
t_f	Fall Time	$I_{B2} = 15\text{ mA}$			60	ns

* Pulsed: Pulse duration = 300 μs , duty cycle $\leq 1.5\%$

** Only for STZT2222A

SOT223 MECHANICAL DATA

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a	2.27	2.3	2.33	89.4	90.6	91.7
b	4.57	4.6	4.63	179.9	181.1	182.3
c	0.2	0.4	0.6	7.9	15.7	23.6
d	0.63	0.65	0.67	24.8	25.6	26.4
e1	1.5	1.6	1.7	59.1	63	66.9
e4			0.32			12.6
f	2.9	3	3.1	114.2	118.1	122.1
g	0.67	0.7	0.73	26.4	27.6	28.7
l1	6.7	7	7.3	263.8	275.6	287.4
l2	3.5	3.5	3.7	137.8	137.8	145.7
L	6.3	6.5	6.7	248	255.9	263.8



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